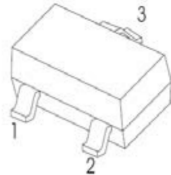


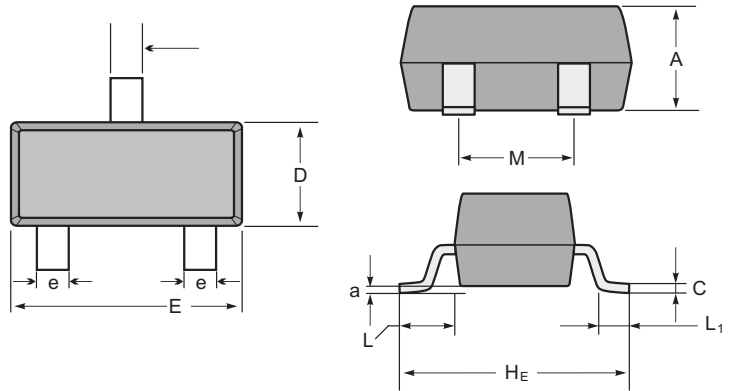
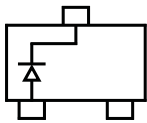
FEATURES

- Fast switching speed.
- For general purpose switching applications.
- High conductance.



Marking

MMBD914:KA2



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Maximum Ratings @Ta=25°C

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V _{RWM}	100	V
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	75	V
Forward Continuous Current	I _{FM}	300	mA
Average Rectified Output Current	I _O	200	mA
Peak Forward Surge Current @t=1.0µs @ t=1.0s	I _{FSM}	2.0 1.0	A
Power Dissipation	P _D	350	mW
Thermal Resistance Junction to Ambient	R _{thJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

MMBD914

Electrical Characteristics@Ta=25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _{(BR)1}	I _R =100μA	100			V
	V _{(BR)2}	I _R =5 uA	75			V
Forward voltage	V _F	I _F =10mA			1.0	V
Reverse current	I _{R1}	V _R =75V			5.0	uA
	I _{R2}	V _R =25V			25	nA
Capacitance between terminals	C _T	V _R =0V,f=1MHz			4.0	pF
Reverse recovery time	t _{rr}	I _F =I _R =10mA, V _R =6V I _{rr} =0.1X I _R , R _L =100Ω			4.0	ns

RATING AND CHARACTERISTIC CURVES (MMBD914)

Fig.1 Power Derating Curve

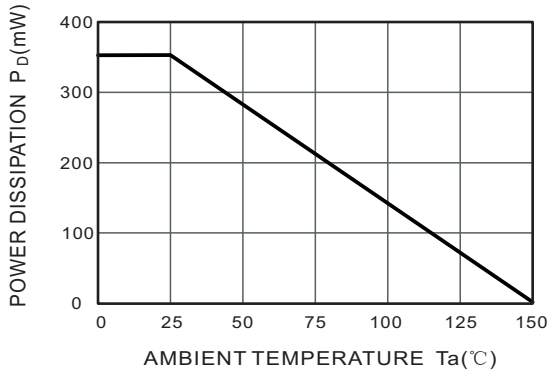


Fig.2 Reverse Characteristics

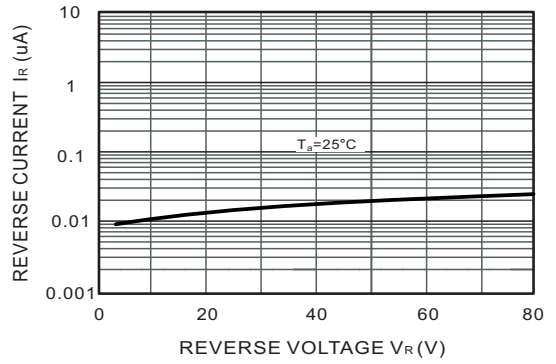


Fig.3 Forward Characteristics

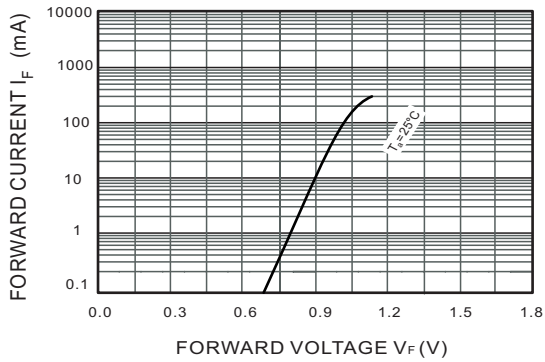


Fig.4 Capacitance Characteristics

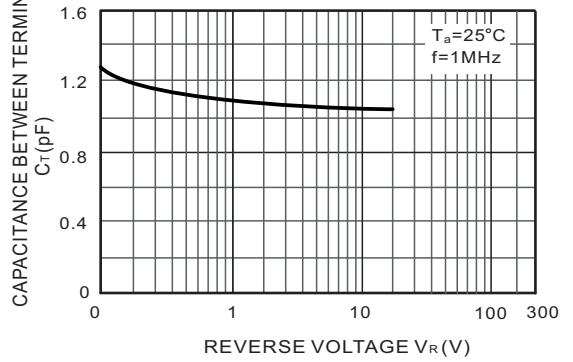


Fig.5 Semiconductor Intrinsic Property

